

Coupler Processing - Vacuum Aspects

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- **Motivation - Breakdown & Vacuum**
- **Bulk Diffusion**
 - diffusing mechanism
 - baking temperatures and times
- **Surface Outgassing**
 - physical background
 - temperatures and binding energies
- **Procedures and Practical Recommendations**

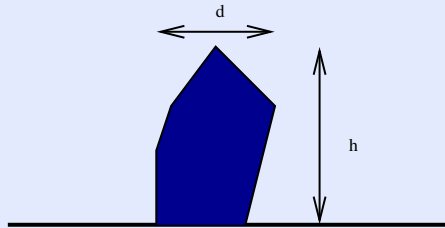
Breakdown Mechanism and Vacuum

electrical breakdown mechanisms are

complicated and not well understood

some common opinions:

- main reason for breakdown: high β_{FN} surface discontinuities or dust particles $E_{\text{peak}} = \beta_{\text{FN}} \cdot E_{\text{avg}}$; roughly: $\beta_{\text{FN}} \propto (h/d)^{1.5 \dots 2}$



- thermally isolated dust particles \rightarrow vaporization, vacuum outburst
- vacuum outburst, ions due to electron bombardment \rightarrow enhances or amplifies breakdown currents

Breakdown Mechanism cont'd.

outgassing is probably **not the primary reason** for breakdown,
but enhances it or lowers the onset-threshold

after longer conditioning and with higher fields the vacuum effect
becomes less important but **breakdowns still happen**

observed e.g. at surface field levels of **300 to 400 MeV/m**;
taking into account typical β_{FN} factors the **tensile strength** of copper
is exceeded!

at these field levels **no temperature dependence** of breakdown limits
between 70 K and 570 K was observed!

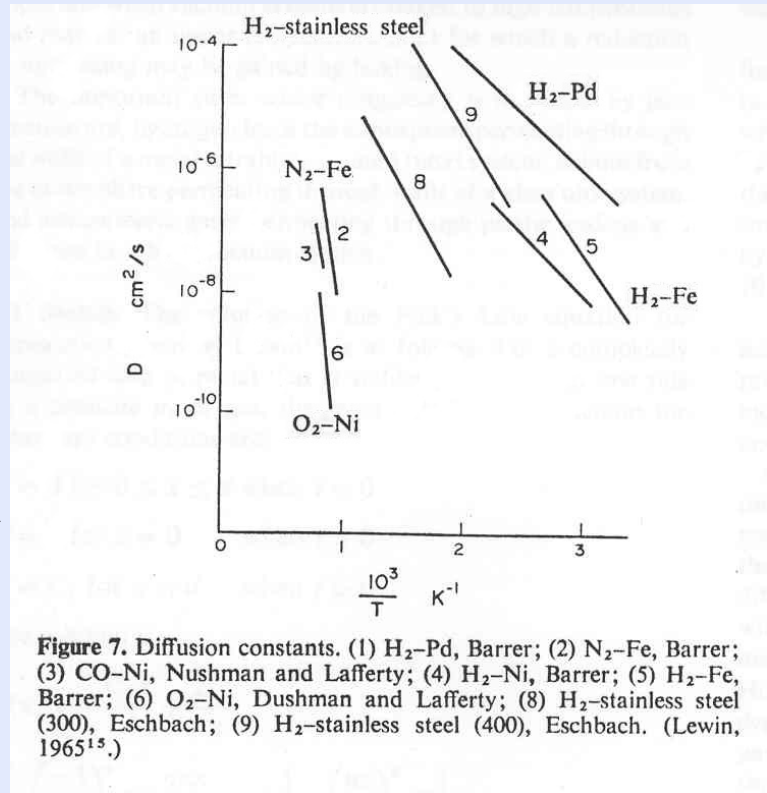
see paper by [W. Wünsch et al. \(CLIC\), EPAC 2002](#)

Dissolved Gas - Bulk Diffusion

described by diffusion eq.:

$$\frac{\partial}{\partial t}c(x, t) - D \frac{\partial^2}{\partial x^2}c(x, t) = 0$$

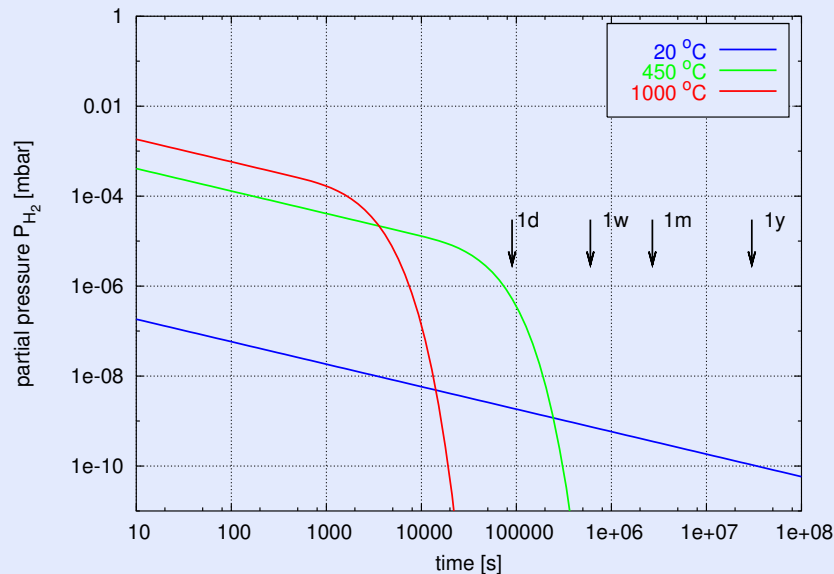
diffusion coefficient D
depends on **temperature** and
gas/material combination



Bulk Diffusion cont'd.

for UHV materials of practical use **only** H_2 has relevant diffusion speed
a common practice is **hydrogen degassing** at $\approx 1000^\circ\text{C}$

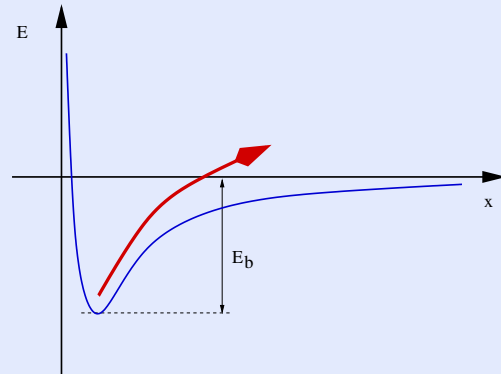
simulation (qualitatively): steel at different temperatures



Surface Gas - Outgassing

- gas molecules are bound to surface

- binding energies below 8 kcal/mol,
→ called **physisorption**



- for larger energies called **chemisorption**

examples of gas-material combinations:

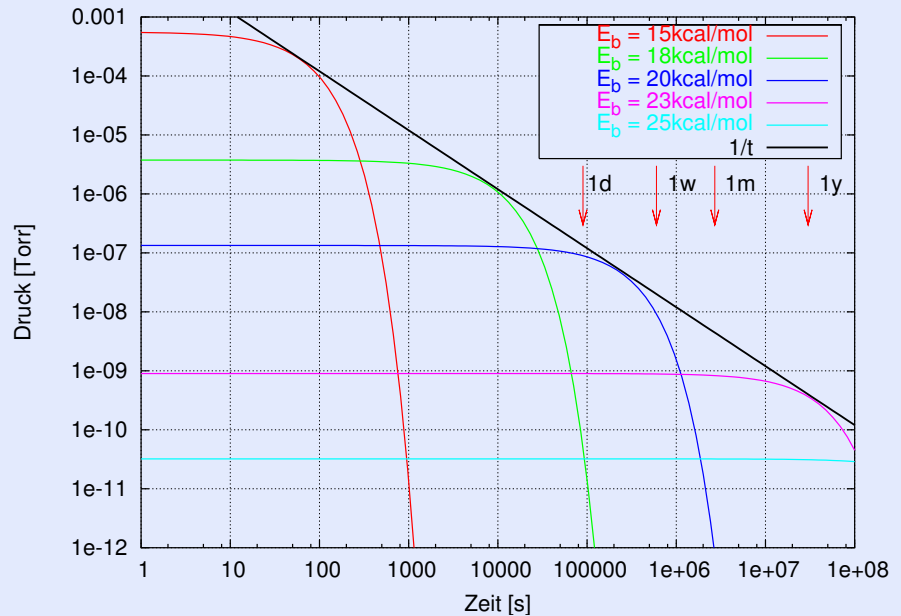
Ar on W	1.9 kcal/mol
H ₂ on Cu	8 kcal/mol
CO on Ni	35 kcal/mol

Surface Gas cont'd.

the binding energy E_b determines how fast a surface is pumped down
average binding period (*sojourn time*):

$$t_s = 10^{-13}[\text{s}] \cdot \exp\left(\frac{E_b}{R_0 T}\right)$$

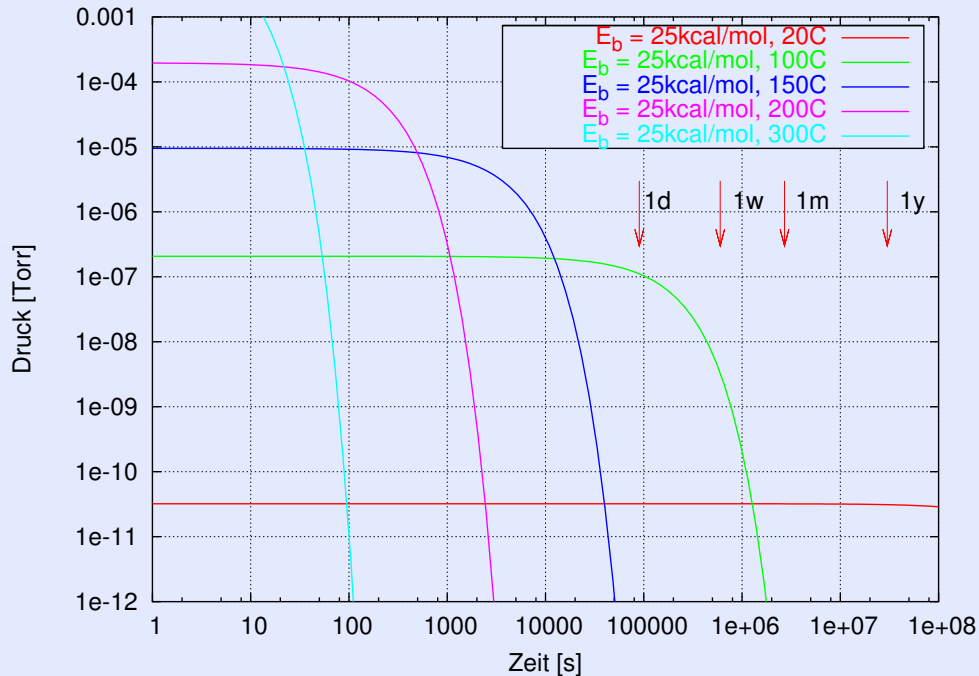
- spectrum of E_b
often complicated
eg. water
- oxide layers,
surface topology
- simulation:
 $A = 15000 \text{ cm}^2$
 $S = 15 \text{ l/s}$
one monolayer



Surface Gas cont'd.

baking can accelerate the pump-down process drastically!

simulation: $E_b = 25$ kcal, different temperatures



Procedures and Recommendations

- H_2 degassing is always advantageous in UHV systems
- baking is very important
 - pumping at elevated temperatures results in exponentially accelerated conditioning
- the temperature dependence is exponential!
 - even small increases of the baking temperature are helpful
- H_2O with its wide spectrum of binding energies is problematic

Recommendations cont'd.

- **conservation** of the conditioning status?
difficult, filling with **dry Nitrogen** will help but:

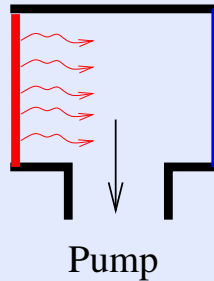
numerical example:

- volume with $V = 4\text{l}$, $A = 1000\text{ cm}^2$, 0.01 mono-layer H_2O
- this are 10^{16} molecules, 300 ng
- when released results in $P_{\text{H}_2\text{O}} \approx 6 \cdot 10^{-4}\text{ mbar!}$

→ **small contaminations with air will degrade the conditioning state quickly**

Recommendations cont'd.

- **partial baking** (surface A hot, B cold)?



not very helpful! - remember:

we are aiming for **orders of magnitude** but this would remove only half(?) of the gas

Conclusions

(neglecting other than vacuum aspects!)

- baking around 150°C for 24 hours would remove the water; higher temperatures 250°C to 400°C would efficiently remove strongly bound hydrocarbons
- in-situ baking is the best option
- ideally the same temperature everywhere
- high pumping speed and efficient cross-sections
- careful cleaning and assembly
this should be unmistakably clear to everybody involved in the production of UHV components!!